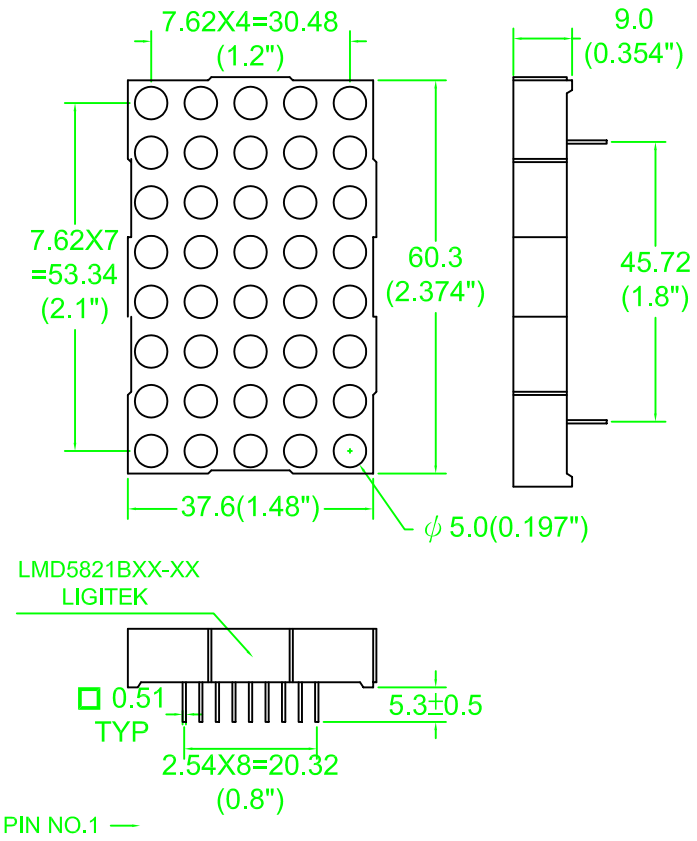
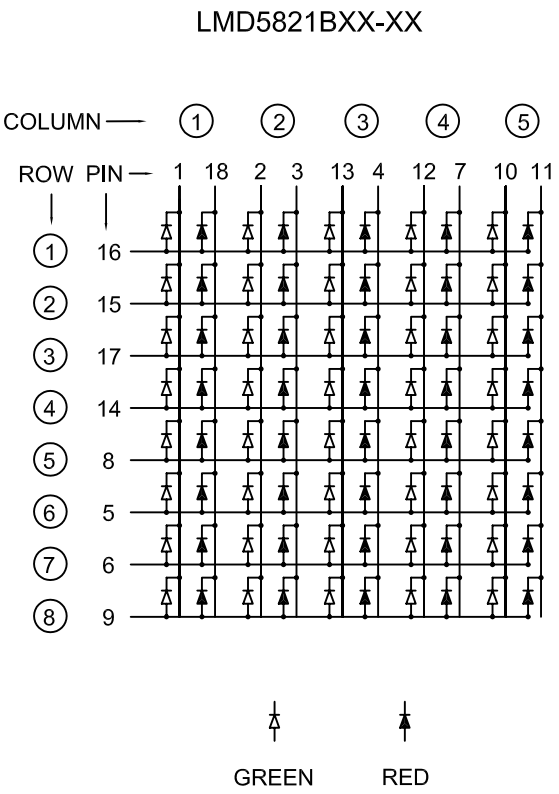
PACKAGE DIMENSION



NOTE:1.All dimension are in millimeters and (Inch)
Tolerance is ±0.25(0.01") unless otherwise noted
2.Specifications are subject to change without notice

INTERNAL CIRCUIT DIAGRAM

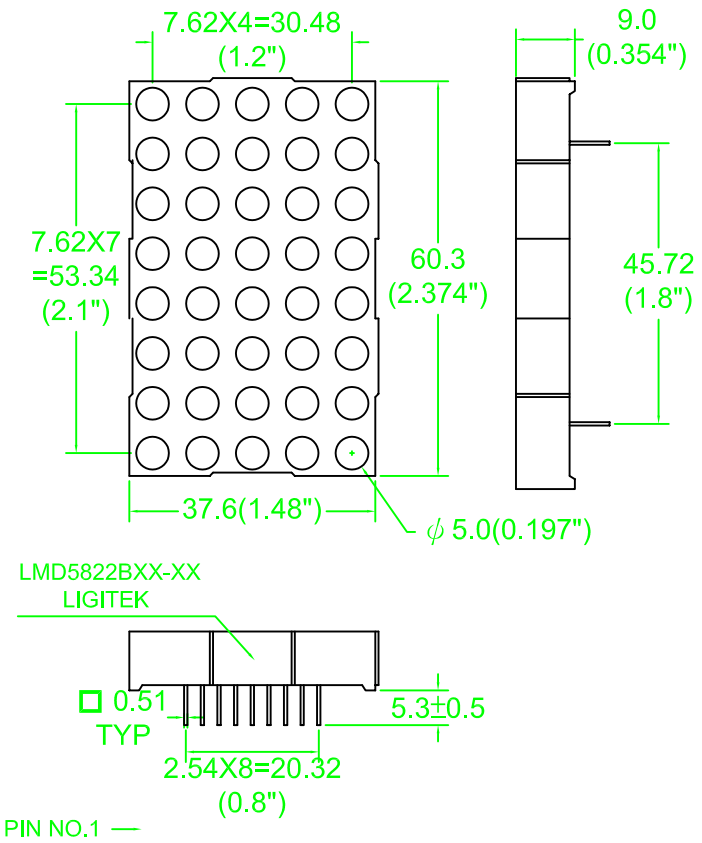


▪ Connection To Electrical Schematic

Electrical connection

PIN NO.	LMD5821BXX-XX	PIN NO.	
1	Cathode Column 1 (Green)	13	Cathode Column 3 (Green)
2	Cathode Column 2 (Green)	14	Anode Row 4
3	Cathode Column 2 (Red)	15	Anode Row 2
4	Cathode Column 3 (Red)	16	Anode Row 1
5	Anode Row 6	17	Anode Row 3
6	Anode Row 7	18	Cathode Column 1(Red)
7	Cathode Column 4 (Red)		
8	Anode Row 5		
9	Anode Row 8		
10	Cathode Column 5 (Green)		
11	Cathode Column 5 (Red)		
12	Cathode Column 4 (Green)		

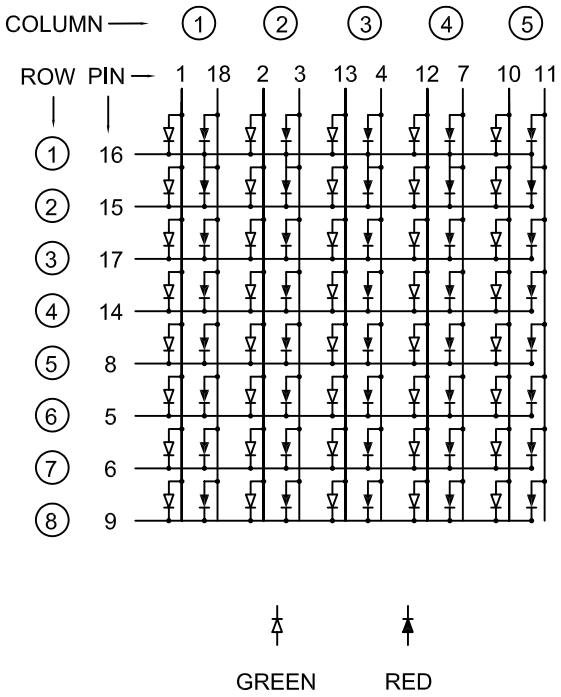
PACKAGE DIMENSION



NOTE:1.All dimension are in millimeters and (Inch)
Tolerance is ±0.25(0.01") unless otherwise noted
2.Specifications are subject to change without notice

INTERNAL CIRCUIT DIAGRAM

LMD5822BXX-XX



▪ Connection To Electrical Schematic

Electrical connection

PIN NO.	LMD5822BXX-XX	PIN NO.	
1	Anode Column 1 (Green)	14	Cathode Row 4
2	Anode Column 2 (Green)	15	Cathode Row 2
3	Anode Column 2 (Red)	16	Cathode Row 1
4	Anode Column 3 (Red)	17	Cathode Row 3
5	Cathode Row 6	18	Anode Column 1 (Red)
6	Cathode Row 7		
7	Anode Column 4 (Red)		
8	Cathode Row 5		
9	Cathode Row 8		
10	Anode Column 5 (Green)		
11	Anode Column 5 (Red)		
12	Anode Column 4 (Green)		
13	Anode Column 3 (Green)		

• Part Selection And Application Information(Ratings At 25℃ Ambient)

PART NO	CHIP		common cathode or anode	λ p (nm)	△λ (nm)	Electrial					IV-M
						Vf(v)			Iv(mcd)		
	material	*emitted*				*Min*	Typ	*Max*	*Min*	Typ	
LMD5821BEGR-XX	GaAsP/GaP	Orange	Column Cathode Row Anode	640	45	1.7	2.0	2.8	1.75	3.05	2:1
	GaP	Green		565	30	1.7	2.1	2.8	3.05	5.0	2:1
LMD5821BSRVG-XX	GaAlAs	Red		660	20	1.5	1.7	2.4	6.1	10.5	2:1
	GaP	Green		565	30	1.7	2.1	2.8	4.0	7.2	2:1
LMD5822BEGR-XX	GaAsP/GaP	Orange	Column Anode Row Cathode	640	45	1.7	2.0	2.8	1.75	3.05	2:1
	GaP	Green		565	30	1.7	2.1	2.8	3.05	5.0	2:1
LMD5822BSRVG-XX	GaAlAs	Red		660	20	1.5	1.7	2.4	6.1	10.5	2:1
	GaP	Green		565	30	1.7	2.1	2.8	4.0	7.2	2:1

▪ Absoult Maximum Rating (Ta=25℃)

Parameter	Red			Green		Yellow			Orange		Unit	Remark
Forward Current Per Chip	SR			VG	G					E		
	40			30	30					30	**mA**	
Peak Current Per Chip (Duty 1/10,0.1mS Pulse Width)	200			120	120					120	**mA**	
Power Dissipation Per Chip	110			100					100		**mW**	
Derating Linear From 25℃ Per Chip	0.45			0.45					0.45		**mA/℃**	
Reverse Current Per Any Chip	10			10					10		**μA**	
Operating Temperature	-25℃ TO +85℃											
Storage Temperature	-25℃ TO +85℃											

Solder Temperature 1-16 Inch Below Seating Plane For 3 Seconds At 260℃

▪ Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Emission Wavelength	λ p	nm	If=20mA
Spectral Line Half-Width	△λ	nm	If=20mA
Reverse Current Any Chip	Ir	μA	Vr=5V
Luminous Intensity Matching Ratio	IV-M		